

# Sergey N Filimonov

## List of Publications by Year in descending order

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35  
papers

402  
citations

933447

10  
h-index

794594

19  
g-index

35  
all docs

35  
docs citations

35  
times ranked

456  
citing authors

#	ARTICLE	IF	CITATIONS
1	Surface Strain-Induced Collective Switching of Ensembles of Molecules on Metal Surfaces. <i>Journal of Physical Chemistry Letters</i> , 2020, 11, 2277-2283.	4.6	4
2	Switchable Schottky Contacts: Simultaneously Enhanced Output Current and Reduced Leakage Current. <i>Journal of the American Chemical Society</i> , 2019, 141, 1628-1635.	13.7	43
3	Principles of Design for Substrate-Supported Molecular Switches Based on Physisorbed and Chemisorbed States. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 26772-26780.	8.0	15
4	Kinetic Model of the Initial Stage of the Nanowire Growth. <i>Russian Physics Journal</i> , 2018, 60, 2040-2043.	0.4	2
5	Molecular Seesaw: Intricate Dynamics and Versatile Chemistry of Heteroaromatics on Metal Surfaces. <i>Journal of Physical Chemistry Letters</i> , 2017, 8, 1235-1240.	4.6	6
6	Monte Carlo Simulations of the Adsorption of Anisotropic Noninteracting Molecules on the (111) Surface of a FCC Crystal. <i>Russian Physics Journal</i> , 2016, 58, 1676-1680.	0.4	0
7	Step Flow Model of Radial Growth and Shape Evolution of Semiconductor Nanowires. <i>Russian Physics Journal</i> , 2016, 59, 1206-1212.	0.4	2
8	On the Influence of Transitions Between Distinct Adsorption States on the Desorption Kinetics of Molecules. <i>Russian Physics Journal</i> , 2016, 59, 762-767.	0.4	1
9	Evaluations of crystal defects of 3C-SiC(1 $\hat{A}$ 1 $\hat{A}$ 1 $\hat{A}$ ) film on Si(110) substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2016, 213, 1125-1129.	1.8	4
10	Formation of qualified epitaxial graphene on Si substrates using two-step heteroepitaxy of C-terminated 3C-SiC(-1-1-1) on Si(110). <i>Diamond and Related Materials</i> , 2016, 67, 51-53.	3.9	6
11	Model of step propagation and step bunching at the sidewalls of nanowires. <i>Journal of Crystal Growth</i> , 2015, 427, 60-66.	1.5	12
12	In Situ SR-XPS Observation of Ni-Assisted Low-Temperature Formation of Epitaxial Graphene on 3C-SiC/Si. <i>Nanoscale Research Letters</i> , 2015, 10, 421.	5.7	14
13	Kinetics of Step Propagation at the Sidewalls of 3D Islands and Nanowires. <i>E-Journal of Surface Science and Nanotechnology</i> , 2014, 12, 68-74.	0.4	4
14	Silicon Carbide on Silicon (110): Surface Structure and Mechanisms of Epitaxial Growth. <i>Russian Physics Journal</i> , 2014, 56, 1439-1444.	0.4	6
15	Direct measurement of surface stress during Bi-mediated Ge growth on Si. <i>Surface Science</i> , 2013, 609, 157-160.	1.9	1
16	Molecular switches from benzene derivatives adsorbed on metal surfaces. <i>Nature Communications</i> , 2013, 4, 2569.	12.8	82
17	Kinetics of two-dimensional island nucleation on reconstructed surfaces. <i>Physical Review B</i> , 2012, 85,	3.2	6
18	Selective Adsorption of $C_{60}$ on $Ge/Si$ Nanostructures. <i>Physical Review Letters</i> , 2012, 108, 116101.	7.8	5

#	ARTICLE	IF	CITATIONS
19	Step bunching and step "rotation" in homoepitaxial growth of Si on Si(110)-16Å <sup>2</sup> . Surface Science, 2011, 605, 838-843.	1.9	6
20	Growth Rate Anomaly in Ultralow-Pressure Chemical Vapor Deposition of 3C-SiC on Si(001) Using Monomethylsilane. Japanese Journal of Applied Physics, 2011, 50, 010203.	1.5	10
21	Growth Rate Anomaly in Ultralow-Pressure Chemical Vapor Deposition of 3C-SiC on Si(001) Using Monomethylsilane. Japanese Journal of Applied Physics, 2011, 50, 010203.	1.5	8
22	Low-Temperature, Low-Pressure and Ultrahigh-Rate Growth of Single-Crystalline 3C-SiC on Si Substrate by ULP-CVD Using Organosilane. Materials Science Forum, 2010, 645-648, 147-150.	0.3	2
23	Kink-formation kinetics and submonolayer density of magic two-dimensional islands in molecular beam epitaxy. Physical Review E, 2009, 80, 051603.	2.1	3
24	Identification of Ge/Si Intermixing Processes at the Bi/Ge/Si(111) Surface. Physical Review Letters, 2007, 98, 166104.	7.8	21
25	Multistage nucleation of two-dimensional Si islands on $\langle \text{Si} \rangle$ MBE growth: STM experiments and extended rate-equation model. Physical Review B, 2007, 76, .	3.2	19
26	Si nucleation on Si(111)-7Å <sup>2</sup> : From cluster pairs to 2D islands. Surface Science, 2007, 601, 3876-3880.	1.9	5
27	Step permeability effect and interlayer mass-transport in the Ge/Si(111) MBE. Materials Science in Semiconductor Processing, 2005, 8, 31-34.	4.0	3
28	Dislocation networks in conventional and surfactant-mediated Ge/Si(111) epitaxy. Surface Science, 2005, 599, 76-84.	1.9	20
29	Scaling of submonolayer island sizes in surfactant-mediated epitaxy of semiconductors. Physical Review B, 2004, 70, .	3.2	23
30	"Rotating" steps in Si(001) homoepitaxy. Surface Science, 2004, 549, 31-36.	1.9	10
31	Terrace-edge-kink model of atomic processes at the permeable steps. Surface Science, 2004, 553, 133-144.	1.9	40
32	Influence of strain on binding energies of Si atoms at Ge() surfaces. Surface Science, 2002, 512, L335-L340.	1.9	3
33	High-Rate Rotated Epitaxy of 3C-SiC(111) on Si(110) Substrate for Qualified Epitaxial Graphene on Silicon. Materials Science Forum, 0, 740-742, 327-330.	0.3	1
34	Rotated Epitaxy of 3C-SiC(111) on Si(110) Substrate Using Monomethylsilane-Based Gas-Source Molecular-Beam Epitaxy. Materials Science Forum, 0, 740-742, 339-343.	0.3	7
35	&lt;i>Ab Initio&/i> Calculations of Absolute Surface Energies of Clean and Hydrogen Covered 3C-SiC(001), (110) and (111) Surfaces. Materials Science Forum, 0, 821-823, 363-366.	0.3	8